

Features

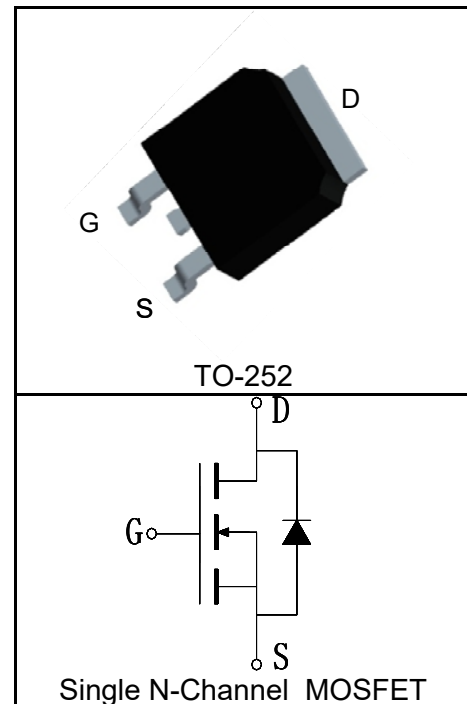
- 40V/65A,
 $R_{DS(ON)} = 7m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 10m\Omega(Typ.)@V_{GS}=4.5V$
- Low $R_{DS(ON)}$
- Super High Dense Cell Design
- Reliable and Rugged

Applications

- Power Switching Appliaction
- Load Switching



Pin Description



Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		40	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		175	°C
T _{STG}	Storage Temperature Range		-55 to 175	°C
I _S	Diode Continuous Forward Current	T _C =25°C	65	A
Mounted on Large Heat Sink				
I _{DP} ^①	300μs Pulse Drain Current Tested	T _C =25°C	260	A
I _D ^②	Continuous Drain Current(V _{GS} =10V)	T _C =25°C	65	A
		T _C =100°C	45	
P _D	Maximum Power Dissipation	T _C =25°C	53	W
		T _C =100°C	26	
R _{θJC}	Thermal Resistance-Junction to Case		2.8	°C/W
R _{θJA} ^③	Thermal Resistance-Junction to Ambient		100	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^④	Avalanche Energy, Single Pulsed		196	mJ

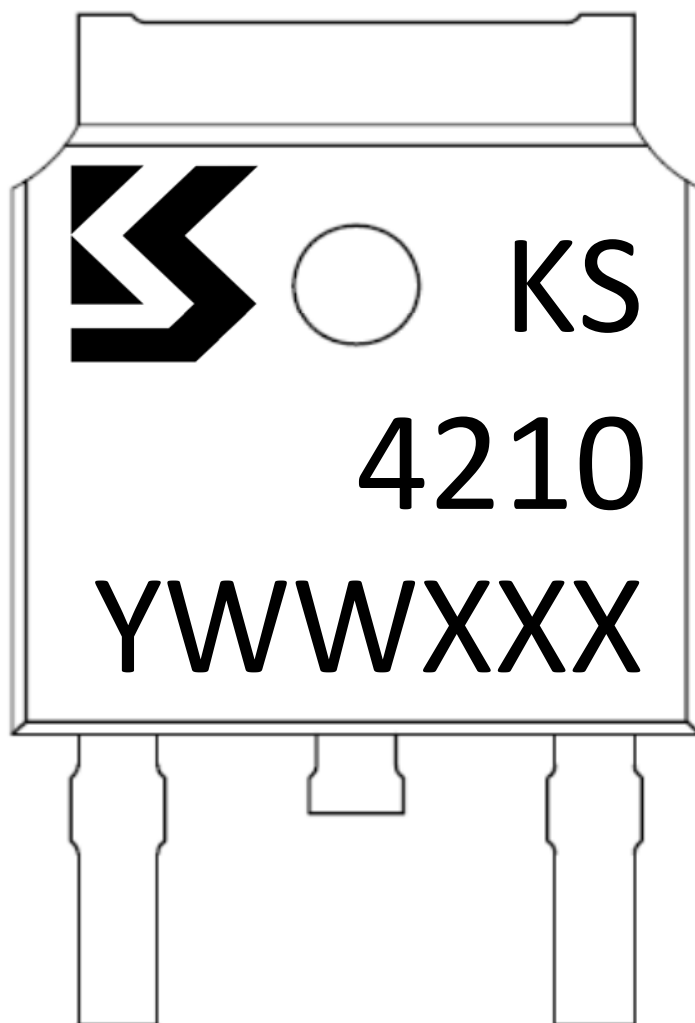
Electrical Characteristics ($T_C=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter	Test Condition	KS4210DA			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	40			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V			1	μA
		T _J =125°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	1.5	2.5	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^⑤	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =20A		7	9	mΩ
		V _{GS} =4.5V, I _{DS} =16A		10	15	mΩ
Diode Characteristics						
V _{SD} ^⑤	Diode Forward Voltage	I _{SD} =20A, V _{GS} =0V		0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =20A, dI _{SD} /dt=100A/μs		13		ns
Q _{rr}	Reverse Recovery Charge			52		nC
Dynamic Characteristics ^⑥						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		1.5		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =20V, Frequency=1.0MHz		2080		pF
C _{oss}	Output Capacitance			160		
C _{rss}	Reverse Transfer Capacitance			130		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =20V, I _{DS} =20A, V _{GEN} =10V, R _G =3Ω		13		ns
t _r	Turn-on Rise Time			37		
t _{d(OFF)}	Turn-off Delay Time			50		
t _f	Turn-off Fall Time			12		
Gate Charge Characteristics ^⑥						
Q _g	Total Gate Charge	V _{DS} =20V, V _{GS} =10V, I _{DS} =20A		48		nC
Q _{gs}	Gate-Source Charge			6		
Q _{gd}	Gate-Drain Charge			13		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 60A.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} , $I_{AS}=28A$, $L=0.5\text{mH}$, $V_{DD}=30V$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

Ordering and Marking Information

Device	Package	Packaging	Quantity	Reel Size	Tape width
KS4210DA	TO-252	Tape&Reel	2500	13"	16mm

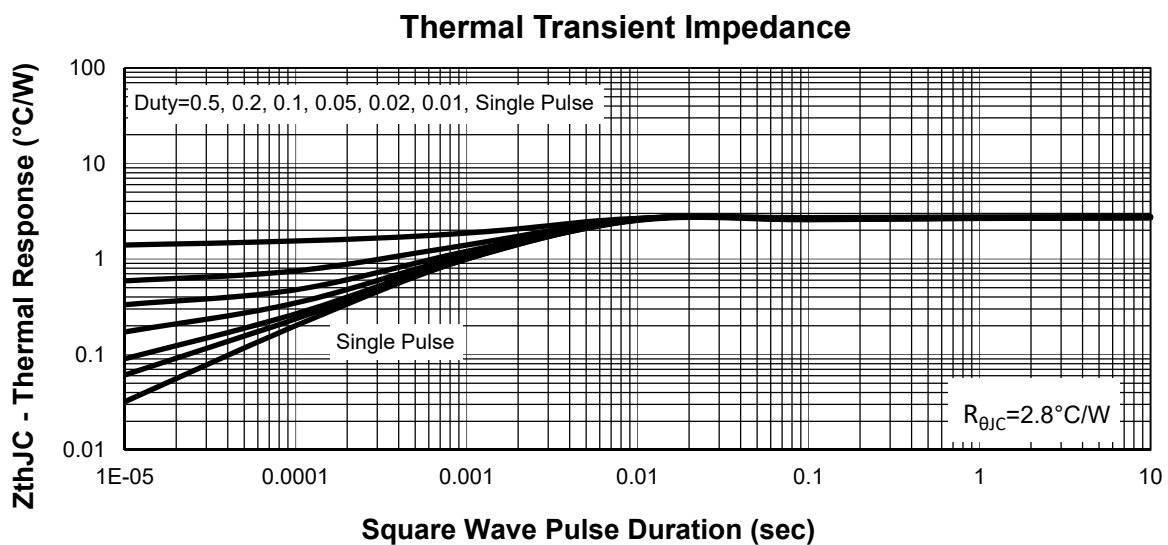
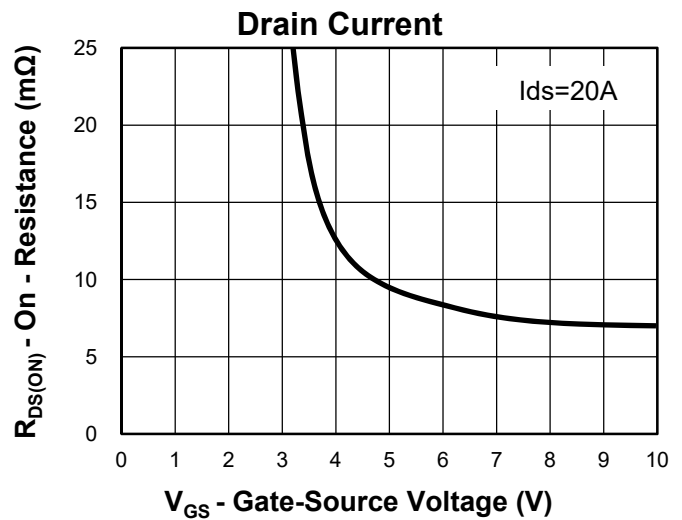
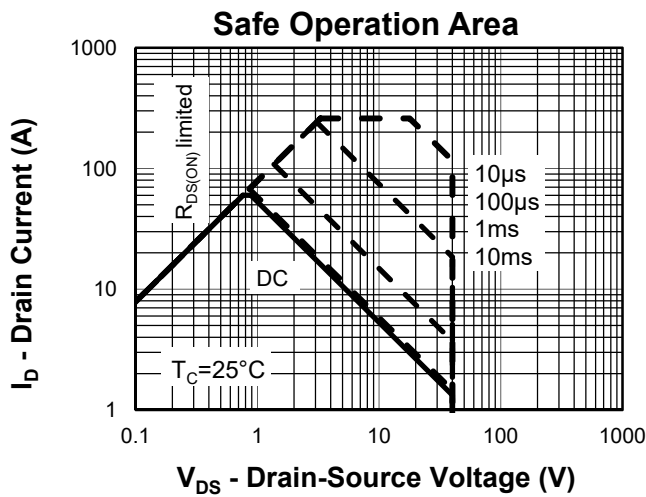
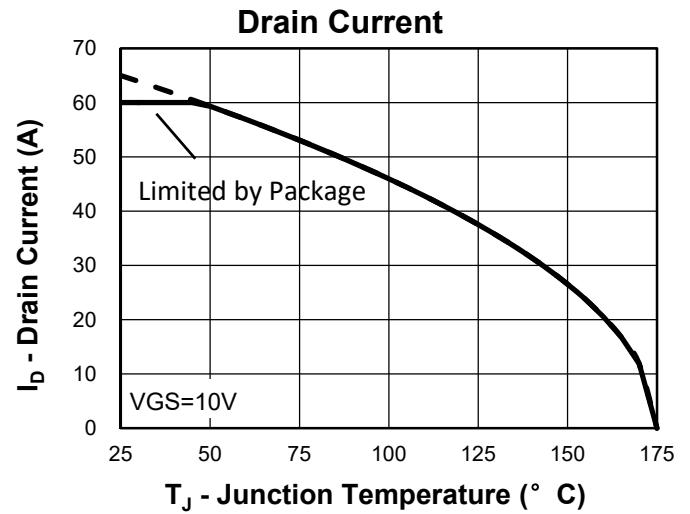
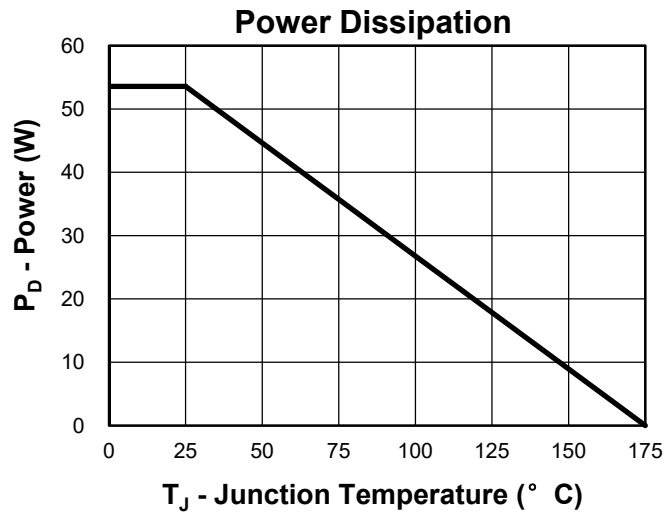


Y =Year,2017-A,2018-B,etc.

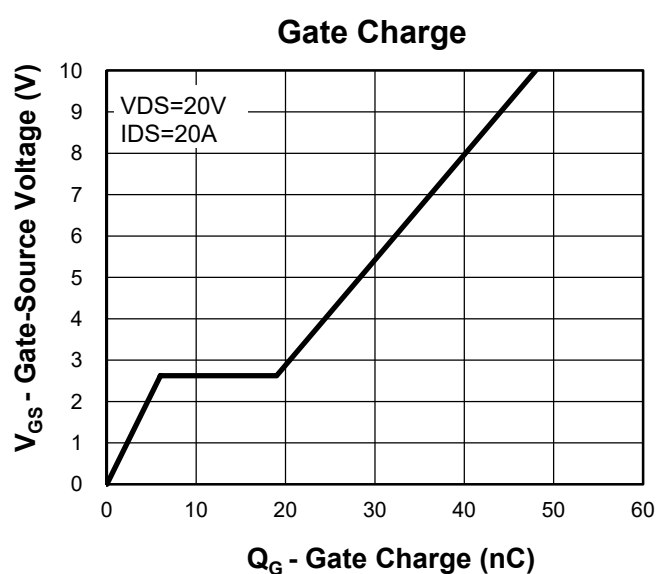
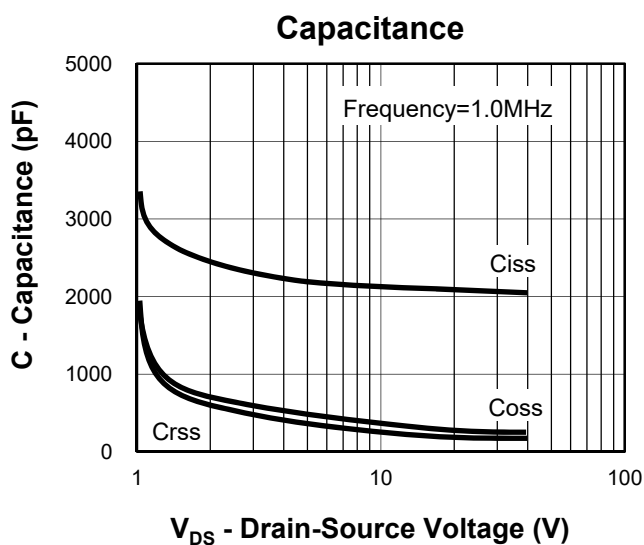
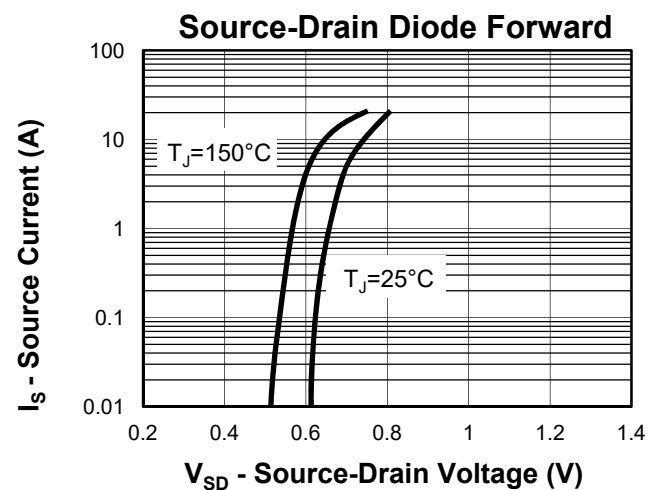
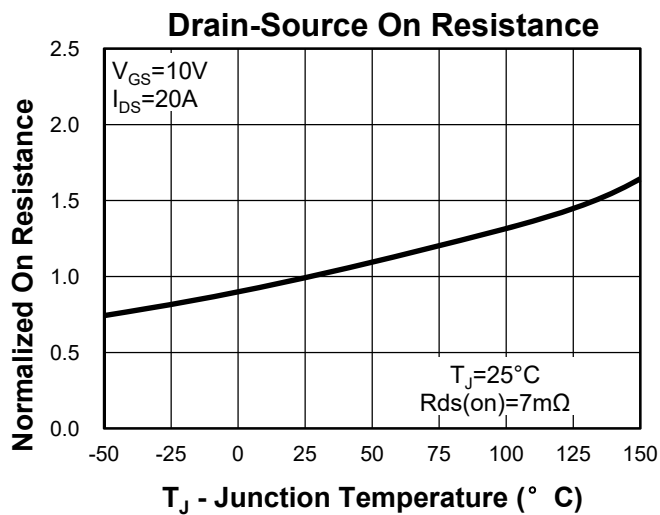
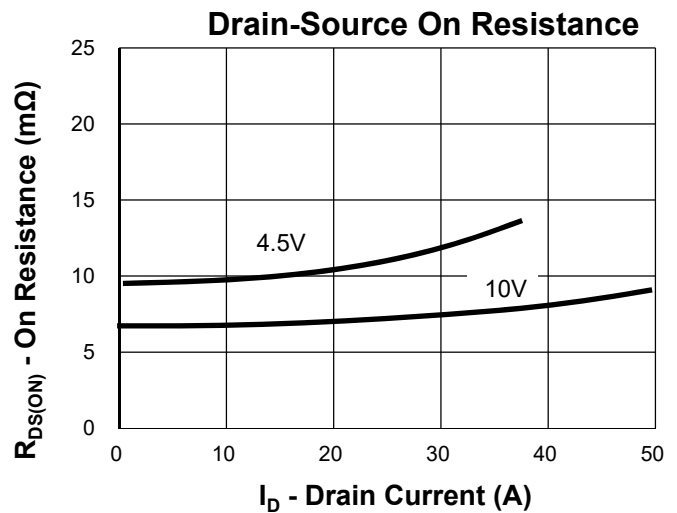
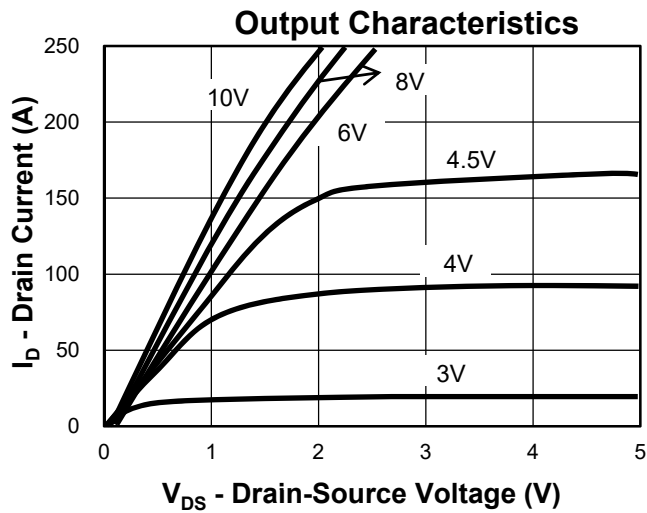
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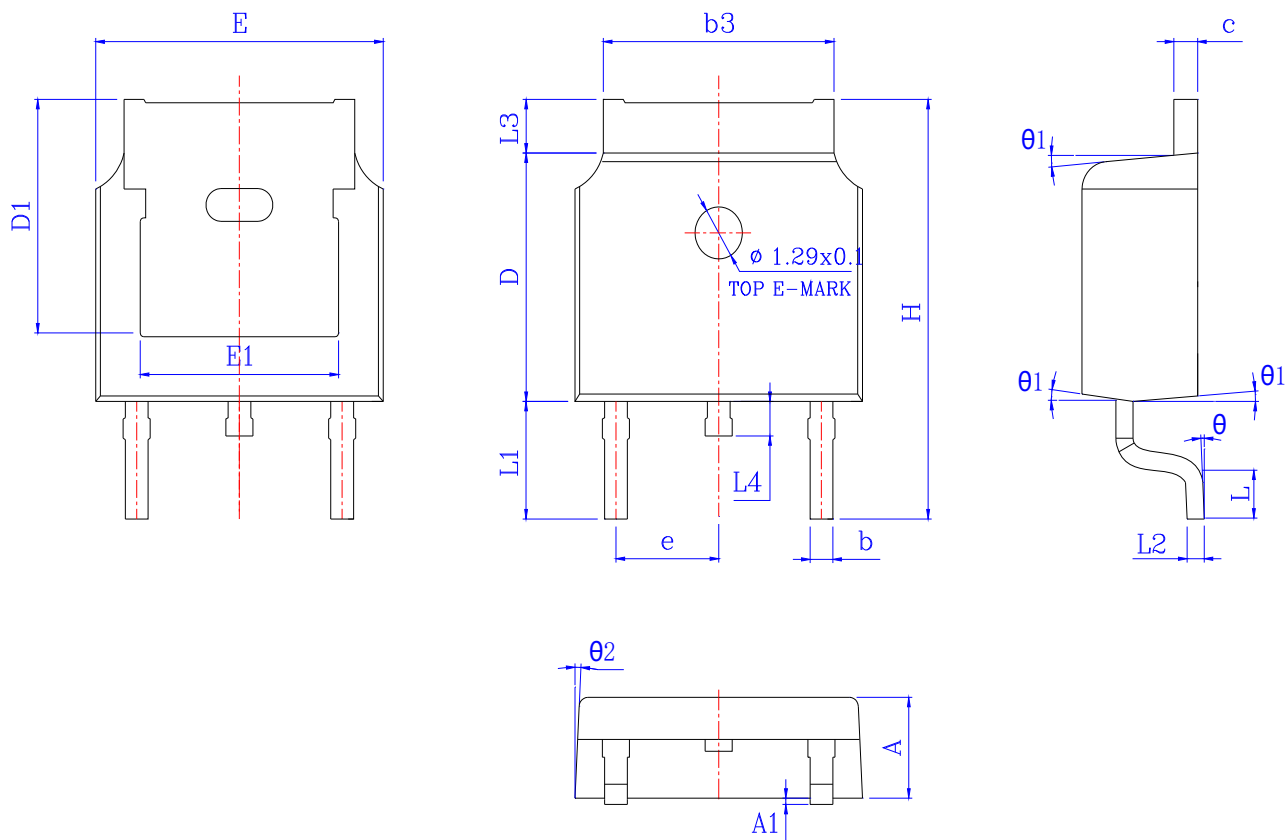
XXX =Lot number.

Typical Characteristics



Typical Characteristics



Package Information
TO-252


SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.200	2.300	2.400	0.087	0.091	0.094
A1	*	*	0.100	*	*	0.004
b	0.660	0.760	0.860	0.026	0.030	0.034
b3	5.130	5.295	5.460	0.202	0.208	0.215
c	0.470	0.535	0.600	0.019	0.021	0.024
D	6.000	6.100	6.200	0.236	0.240	0.244
D1	5.30 REF			0.20 REF		
E	6.500	6.600	6.700	0.256	0.260	0.264
E1	4.700	4.810	4.920	0.185	0.189	0.194
e	2.28 REF			0.09 REF		
H	9.800	10.100	10.400	0.386	0.398	0.409
L	1.400	1.550	1.700	0.055	0.061	0.067
L1	2.743 REF			0.108 REF		
L2	0.510 BSC			0.020 BSC		
L3	0.900	1.075	1.250	0.035	0.042	0.049
L4	0.600	0.800	1.000	0.024	0.031	0.039
θ	0°	*	8°	0°	*	8°
$\theta 1$	5°	7°	9°	5°	7°	9°
$\theta 2$	5°	7°	9°	5°	7°	9°

Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms



Diode Recovery Test Circuit and Waveforms



Gate Charge Test Circuit and Waveform



Customer Service

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